



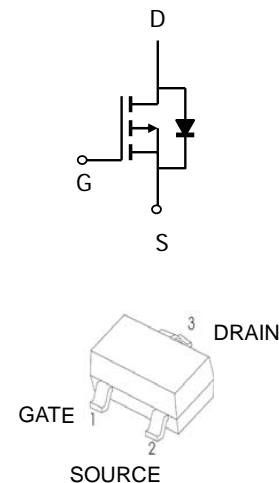
**迈拓电子**  
MAITUO ELECTRONIC

## MT3407 Plastic-Encapsulate MOSFETs

### General Description

The MT3407 uses advanced trench technology to provide excellent  $R_{DS(on)}$  with low gate charge. This device is suitable for use as a load switch or in PWM applications.

**MARKING: 3407**



**Maximum ratings ( $T_a=25^\circ\text{C}$  unless otherwise noted)**

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	-4.1	A
Power Dissipation	$P_D$	350	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55~+150	$^\circ\text{C}$

**Electrical characteristics ( $T_a=25^\circ\text{C}$  unless otherwise noted)**

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Static characteristics</b>						
Drain-source breakdown voltage	$BV_{DSS}$	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$	-30			V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = -24\text{V}, V_{GS} = 0\text{V}$			-1	$\mu\text{A}$
Gate-source leakage current	$I_{GS}$	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$			$\pm 100$	nA
Drain-source on-resistance (note 1)	$R_{DS(on)}$	$V_{GS} = -10\text{V}, I_D = -4.1\text{A}$			60	$\text{m}\Omega$
		$V_{GS} = -4.5\text{V}, I_D = -3\text{A}$			87	$\text{m}\Omega$
Forward transconductance (note 1)	$g_{FS}$	$V_{DS} = -5\text{V}, I_D = -4\text{A}$	5.5			S
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	-1		-3	V
Diode forward voltage (note 1)	$V_{SD}$	$I_S = -1\text{A}, V_{GS} = 0\text{V}$			-1	V
<b>Dynamic characteristics (note 2)</b>						
Input capacitance	$C_{iss}$	$V_{DS} = -15\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$		700		pF
Output capacitance	$C_{oss}$			120		pF
Reverse transfer capacitance	$C_{rss}$			75		pF
<b>Switching Characteristics (note 2)</b>						
Turn-on delay time	$t_{d(on)}$	$V_{GS} = -10\text{V}, V_{DS} = -15\text{V}, R_L = 3.6\Omega, R_{GEN} = 3\Omega$		8.6		ns
Turn-on rise time	$t_r$			5.0		ns
Turn-off delay time	$t_{d(off)}$			28.2		ns
Turn-off fall time	$t_f$			13.5		ns

### Notes:

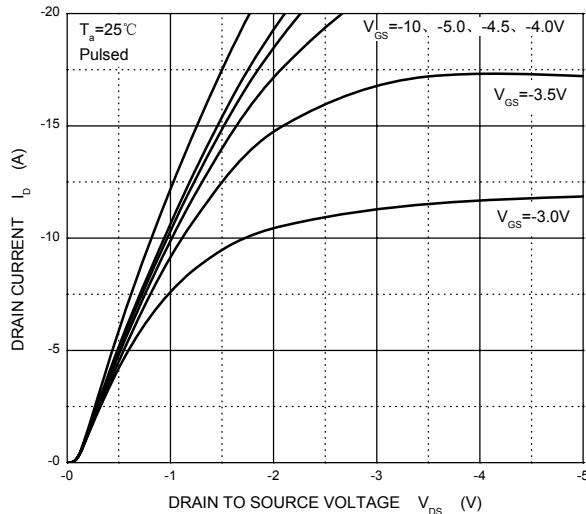
1. Pulse test: Pulse width  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2\%$ .
2. These parameters have no way to verify.



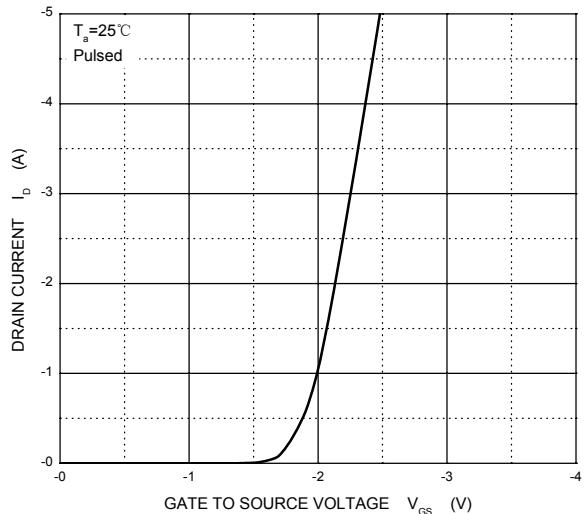
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## Typical Characteristics

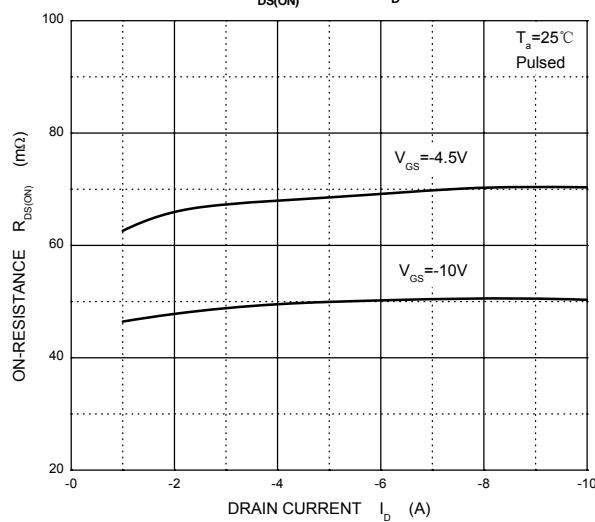
Output Characteristics



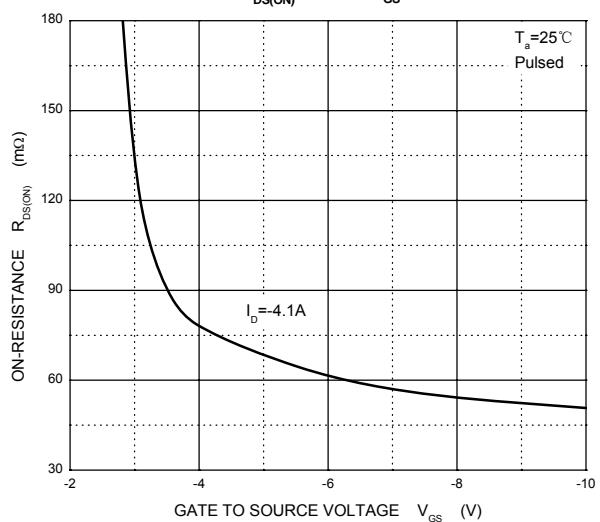
Transfer Characteristics



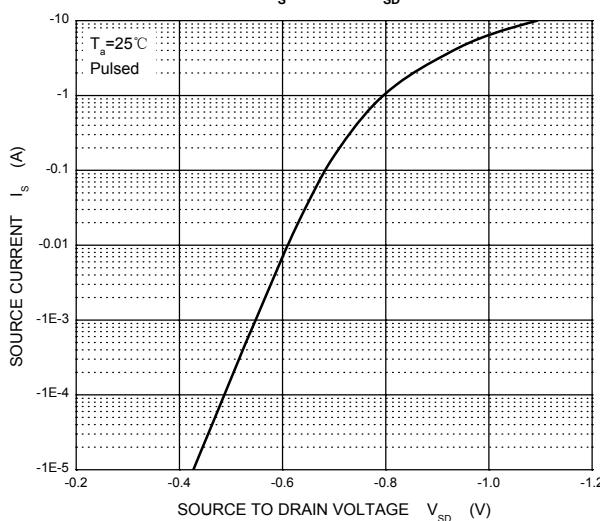
$R_{DS(ON)}$  —  $I_D$



$R_{DS(ON)}$  —  $V_{GS}$



$I_s$  —  $V_{SD}$





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## PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

